

IN THE SPECIFICATION

In the specification on page 1, line 1, please replace the title of the application with the following:

“SEMICONDUCTOR ~~CHIP HAVING BOND PADS AND~~ MULTI-CHIP PACKAGE”

Please replace the paragraph on page 1, starting at line 9 to line 10, with the following:

The present invention relates generally to semiconductor devices and, more particularly, to a semiconductor chip having bond pads ~~and to~~ for a multi-chip package (MCP).

Please replace the paragraph on page 5, starting at line 13 to line 21, with the following:

A passivation layer 16 is formed on the bond pad-wiring pattern 12. An interlayer dielectric (ILD) 13 is then formed on the passivation layer 16. The ILD 13 is made of a material having good insulation and integration properties to protect bond pads 17 from mechanical stress due to subsequent wire bonding, beam lead bonding, or ball bonding. For example, a high-density plasma (HDP) oxidized layer, a benzocyclobutene (BCB) layer, a polybenzoxazole (PBO) layer, or a polyimide layer may be used as the ILD 13. An HDP oxide layer using silan, oxygen and argon gases, for example, an HDP-SiO₂ layer is preferably used. The passivation layer 16 and the ILD 13 have openings 14 (shown in FIGS. 6-7) formed therein to expose predetermined portions of the bond pad-wiring pattern 12a.